

Product data sheet

1. General description

Dual ultrafast power diode in a TO263 (D2PAK) surface-mountable plastic package.

2. Features and benefits

- High reverse voltage surge capability
- High thermal cycling performance
- Low thermal resistance
- Very low on-state loss
- Soft recovery characteristic minimizes power consuming oscillations
- Surface-mountable package

3. Applications

Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Q	uick reference data					
Symbol	Parameter	Conditions		Values		Unit
Absolute	e maximum rating					
V_{RRM}	repetitive peak reverse voltage			200		V
$I_{O(AV)}$	average output current	δ = 0.5; square-wave pulse; T _{mb} ≤ 115 °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u>		20		А
I _{RRM}	repetitive peak reverse current	$δ = 0.001; t_p = 2 μs;$		0.2		А
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = $1.5 \text{ k}\Omega$; all pins		8		kV
Static ch	aracteristics					·
V _F	forward voltage	$I_{F} = 8 \text{ A}; T_{j} = 150 \text{ °C}; Fig. 4$	ΤR	- 0.72	0.85	V
		I _F = 20 A; T _j = 25 °C		- 1	1.15	V
Dynamic	characteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery}; Fig. 5$		- 20	25	ns

5. Pinning information

Table 2.	Pinning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	К	cathode [1]		
3	A2	anode 2		
mb	К	mounting base; cathode	1 TO-263 (D2PAK)	K sym125

[1] it is not possible to make a connection to pin 2 of the TO263 package

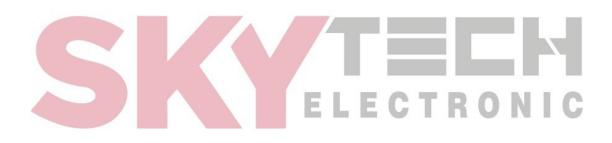
6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part	number	Packing method	Small packing quantity	Package version	Package issue date
BYV32EB-200	TO263	BYV32EB-200,	118	Reel	800	TO263N	26-Sep-2016

7. Marking

Table 4. Marking codes		
Type number	Marking codes	
BYV32EB-200	BYV32EB-200	

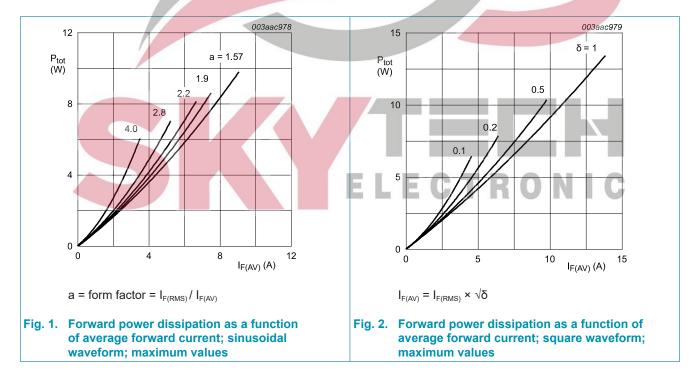


8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		200	V
V_{RWM}	crest working reverse voltage		200	V
V _R	reverse voltage	DC	200	V
I _{O(AV)}	average output current	δ = 0.5; square-wave pulse; T _{mb} ≤ 115 °C; both diodes conducting; <u>Fig 1</u> ; <u>Fig 2</u>	20	А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 115 °C; per diode	20	А
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; sine-wave pulse; T _{j(init)} = 25 °C; per diode	125	А
		t _p = 8.3 ms; sine-wave pulse; T _{j(init)} = 25 °C; per diode	137	A
I _{RRM}	repetitive peak reverse current	δ = 0.001; t _p = 2 µs; per diode	0.2	A
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs; per diode	0.2	A
T _{stg}	storage temperature		-40 to 150	°C
Tj	junction temperature		150	°C
V_{ESD}	electrostatic discharge voltage	HBM; all pins; C = 250 pF; R = $1.5 \text{ k}\Omega$	8	kV



9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; both diodes conducting	-	-	1.6	K/W
		with heatsink compound; per diode; Fig 3	-	-	2.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	60	-	K/W

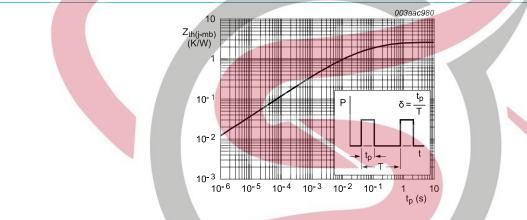


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

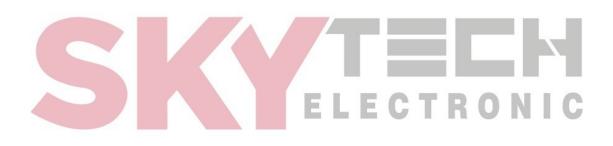
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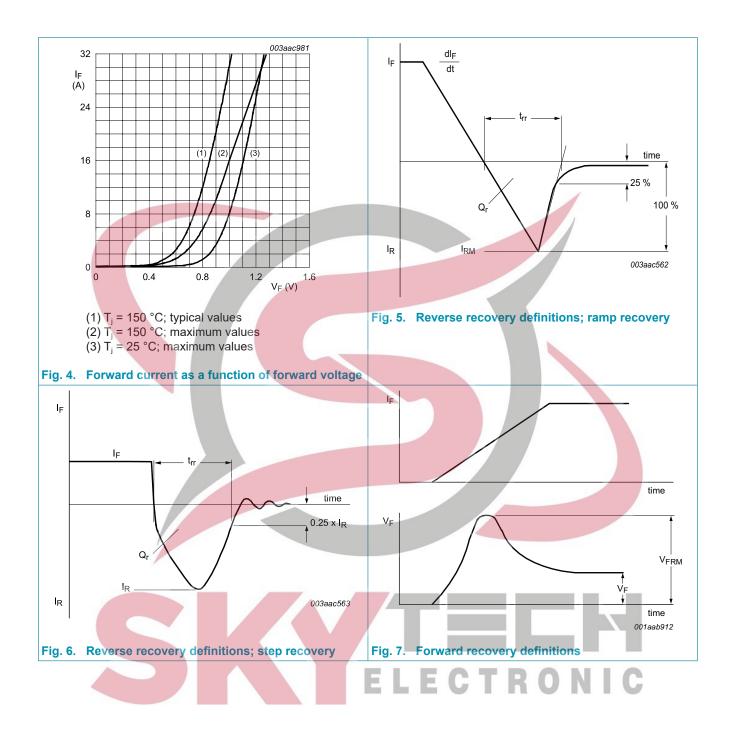
10. Characteristics

Symbol	Parameter	Conditions	Min	Tun	Max	Unit
		Conditions	IVIIII	Тур	IVIAX	Unit
Static cha	racteristics		 			
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	0.72	0.85	V
		I _F = 20 A; T _j = 25 °C	-	1	1.15	V
I _R	reverse current	V _R = 200 V; T _j = 25 °C	-	6	30	μA
		V _R = 200 V; T _j = 100 °C	-	0.2	0.6	mA
Dynamic	characteristics					
Q _r	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{V}; \text{d}_F/\text{d}\text{t} = 20 \text{A}/\mu\text{s}; \\ \text{T}_j = 25 ^\circ\text{C}$	•	8	12.5	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}_F/\text{d}t = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery; Fig. 5}$	- /	20	25	ns
		$I_F = 0.5 \text{ A to } I_R = 1 \text{ A}; T_J = 25 \text{ °C};$ measured at $I_R = 0.25 \text{ A};$ step recovery; Fig. 6	-	10	20	ns
V _{FR}	forward recovery voltage	I _F = 1 A; dI _F /dt = 10 A/μs; T _j = 25 °C; <u>Fig. 7</u>	-	-	1	V



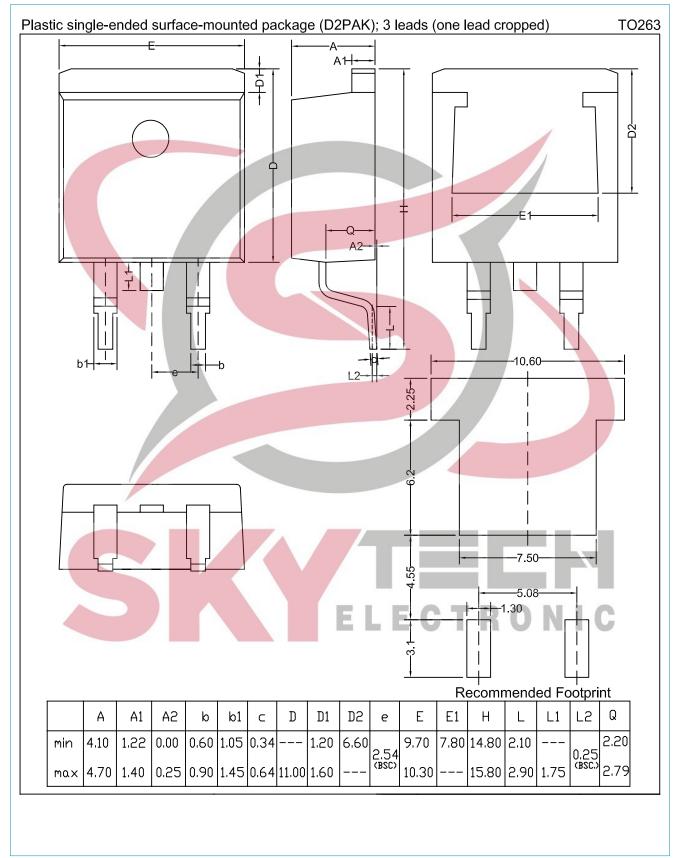
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BYV32EB-200



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11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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